1.5A Ultra-small Load Switch with Slew Rate Control

FEATURES

- Integrated P-channel MOSFET load switch
- Input voltage: 1.2V to 5.5V
- 1.5A maximum continuous switch current
- Switch on-resistance(typ.):
  Rdson=52mΩ at VIN=5.5V
  Rdson=58mΩ at VIN=4.2V
  Rdson=66mΩ at VIN=3.3V
  Rdson=80mΩ at VIN=2.5V
  Rdson=110mΩ at VIN=1.8V
  Rdson=222mΩ at VIN=1.2V
- Controlled slew rate to limit inrush currents
- Internal EN Pull-Down Resistor on AW35122
- Quick output discharge
- FCDFN 1mm×1mm×0.55mm-4L package

APPLICATIONS

- Smartphones and Tablets
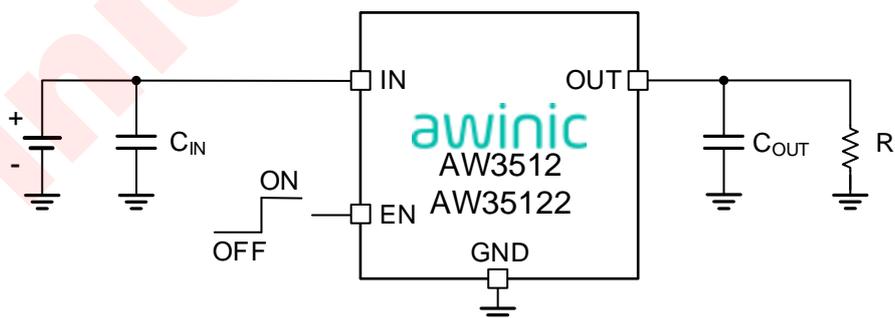- Portable Devices
- Wearables

GENERAL DESCRIPTION

The AW3512/AW35122 is a load switch with output slew rate control. The device integrates a 66mΩ (typ.) P-channel MOSFET, which can operate over a wide input range of 1.2V to 5.5V.

The AW3512/AW35122 features output slew rate control, limiting inrush currents during turn-on to protect downstream devices.

DEVICE COMPARISON TABLE

Part Number	AW3512	AW35122
Top Mark	SV	UJ
EN Pull Down Resistor	NO	7.1MΩ

TYPICAL APPLICATION CIRCUITS

Figure 1　Typical Application circuit of AW3512/AW35122

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PIN CONFIGURATION AND TOP MARK

AW3512FDR
(Top View)

AW3512FDR Marking
(Top View)

SV – AW3512FDR
X – Production Tracing Code

AW35122FDR
(Top View)

AW35122FDR Marking
(Top View)

UJ – AW35122FDR
X – Production Tracing Code
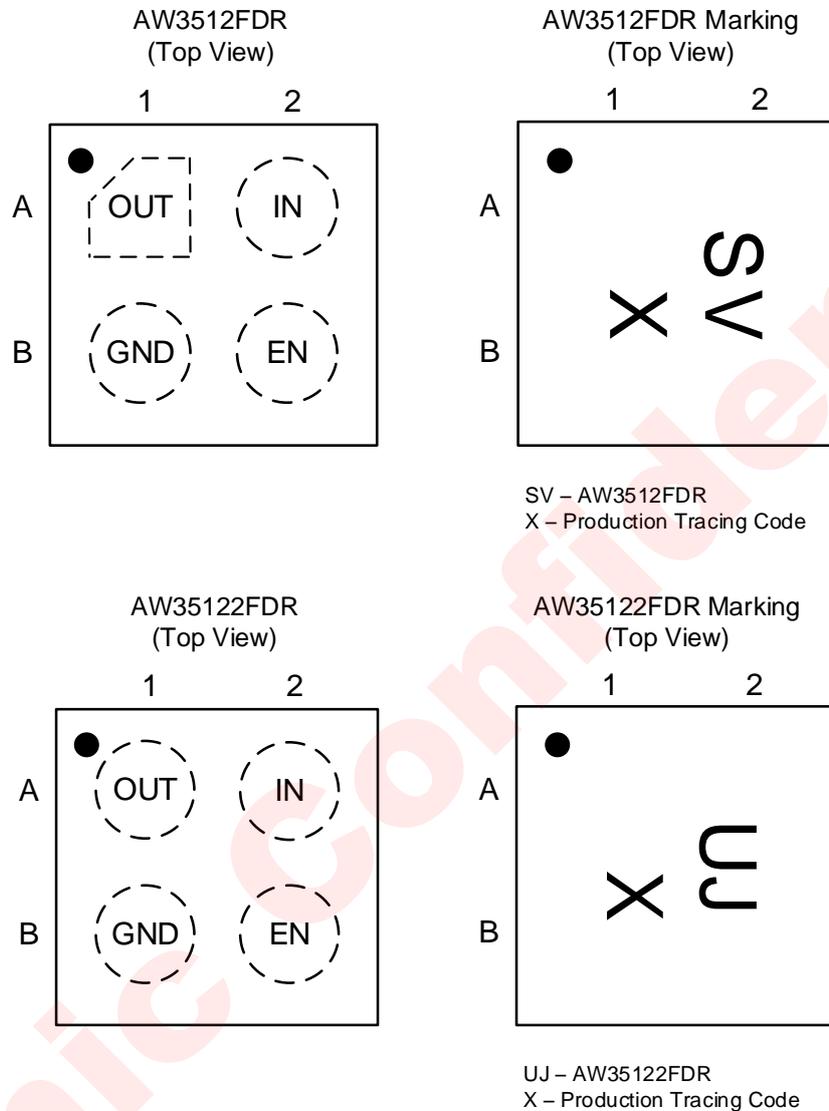
Figure 2   Pin Configuration and Top Mark

PIN DEFINITION

Pin	Name	Description
A1	OUT	Switch output
A2	IN	Switch input and power supply
B1	GND	Device ground
B2	EN	Switch control input, active high, do not leave floating. AW3512.
B2	EN	Switch control input, active high, internal 7.1MΩ pull down resistor. AW35122

FUNCTIONAL BLOCK DIAGRAM

Figure 3   Functional Block Diagram

TYPICAL APPLICATION CIRCUITS

Figure 4   Typical Application circuit of AW3512/AW35122

ORDERING INFORMATION

Part Number	Temperature	Package	Marking	Moisture Sensitivity Level	Environmental Information	Delivery Form
AW3512FDR	-40℃～85℃	FCDFN 1mm×1mm -4L	SV	MSL1	ROHS+HF	3000 units/ Tape and Reel
AW35122FDR	-40℃～85℃	FCDFN 1mm×1mm -4L	UJ	MSL1	ROHS+HF	3000 units/ Tape and Reel

ABSOLUTE MAXIMUM RATINGS(NOTE1)

PARAMETERS		RANGE
Supply Voltage Range V$_{IN}$		-0.3V to 6V
Input Voltage Range	EN	-0.3V to 6V
Output Voltage Range	OUT	-0.3V to 6V
Maximum Continuous Switch Current for VIN ≥ 2V(NOTE 2)		1.5A
Maximum Peak Switch Current for VIN ≥ 2.5V(NOTE 3)		2A
Junction-to-ambient Thermal Resistance θ$_{JA}$(NOTE 4)		166°C/W
Operating Free-air Temperature Range		-40°C to 85°C
Maximum Junction Temperature T$_{JMAX}$		150°C
Storage Temperature T$_{STG}$		-65°C to 150°C
Lead Temperature (Soldering 10 Seconds)		260°C
ESD		
HBM (Human Body Model) (NOTE 5)		±2kV
CDM(Charged Device Model) (NOTE 6)		±1.5kV
MM(Machine Model) (NOTE 7)		±200V
Latch-Up		
Latch-Up (NOTE 8)		+IT：200mA -IT：-200mA

NOTE1: Conditions out of those ranges listed in "absolute maximum ratings" may cause permanent damages to the device. In spite of the limits above, functional operation conditions of the device should within the ranges listed in "recommended operating conditions". Exposure to absolute-maximum-rated conditions for prolonged periods may affect device reliability.

NOTE2: Limited by thermal design.

NOTE3: Limited by thermal design, and tested in 10ms width pulse current.

NOTE4: Thermal resistance from junction to ambient is highly dependent on PCB layout.

NOTE5: The human body model is a 100pF capacitor discharged through a 1.5kΩ resistor into each pin. Test method: ESDA/JEDEC JS-001-2017.

NOTE6: All pins. Test Condition: ESDA/JEDEC JS-002-2014.

NOTE7: All pins. Test Condition: JESD22-A115C.

NOTE8: Test Condition: JESD78E.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
V$_{IN}$	Input Voltage	1.2		5.5	V
V$_{EN}$	EN Voltage	0		5.5	V
V$_{OUT}$	Output Voltage	0		V$_{IN}$	V
C$_{IN}$	Input capacitance	0.1	1		μF
C$_{OUT}$	Output load capacitance	0.1	1		μF

ELECTRICAL CHARACTERISTICS

T_A = -40°C to 85°C unless otherwise noted. Typical values are guaranteed for V_{IN} = 5V, C_{IN} = 1μF, $I_{IN} \leq$ 1.5A and T_A = 25°C.

PARAMETER		TEST CONDITION		MIN	TYP	MAX	UNIT
INPUT CURRENTS							
I_Q	Input quiescent current	V_{IN}=3.3V, V_{EN}=3.3V,I_{OUT}=0A, T_A=25°C			2	12	nA
		V_{IN}=3.3V, V_{EN}=3.3V,I_{OUT}=0A, T_A=85°C			9		nA
		V_{IN}=5.5V, V_{EN}=5.5V,I_{OUT}=0A, T_A=25°C			15	25	nA
		V_{IN}=5.5V, V_{EN}=5.5V,I_{OUT}=0A, T_A=85°C			10		nA
I_{SD}	Shutdown current from IN to GND	V_{IN}=1.2V, V_{EN}=0V, T_A=25°C			2		nA
		V_{IN}=1.8V, V_{EN}=0V, T_A=25°C			2		nA
		V_{IN}=3.3V, V_{EN}=0V, T_A=25°C			6	44	nA
		V_{IN}=4.0V, V_{EN}=0V, T_A=25°C			16		nA
		V_{IN}=4.5V, V_{EN}=0V, T_A=25°C			28		nA
		V_{IN}=5.0V, V_{EN}=0V, T_A=25°C			60	970	nA
		V_{IN}=5.0V, V_{EN}=0V, T_A=55°C			90		nA
		V_{IN}=5.0V, V_{EN}=0V, T_A=85°C			350		nA
		V_{IN}=5.5V, V_{EN}=0V, T_A=25°C			139		nA
I_{LEAKEN}	EN pin leakage current	V_{IN}=0V, V_{EN}=5.0V	AW3512			0.5	μA
			AW35122			1.5	μA
R_{EN}	EN pin pull down resistor	V_{EN}=5.0V, only for AW35122			7.1		MΩ
POWER SWITCH							
R_{dson}	Internal switch MOSFET on-state resistance	V_{IN}=5.5V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			52		mΩ
		V_{IN}=4.2V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			58		
		V_{IN}=3.3V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			66		
		V_{IN}=3.0V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			70	120	
		V_{IN}=1.8V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			110		
		V_{IN}=1.2V, V_{EN}=high, I_{OUT}=200mA, T_A=25°C			222		
R_{DIS}	Output discharge resistance	V_{IN}=3.3V, V_{EN}=low, T_A=25°C	AW3512		276	300	Ω
			AW35122	50	75	100	
t_R	Output rise time	V_{IN}=3.6V, C_{OUT}=1μF, R_{OUT}=30Ω			165		μs
t_F	Output fall time	V_{IN}=3.6V, C_{OUT}=1μF, R_{OUT}=30Ω	AW3512		60		μs
			AW35122		42		

PARAMETER		TEST CONDITION		MIN	TYP	MAX	UNIT
t_{ON}	Switch turn on time	V_{IN}=3.6V, C_{OUT}=1μF, R_{OUT}=30Ω			238		μs
t_{OFF}	Switch turn off time	V_{IN}=3.6V, C_{OUT}=1μF, R_{OUT}=30Ω	AW3512		17		μs
			AW35122		12		
t_{EN}	Enable time	V_{IN}=3.6V, C_{OUT}=1μF, R_{OUT}=30Ω			130		μs
V_{IH}	EN input high threshold level			1.2			V
V_{IL}	EN input low threshold level					0.5	V

TIMING DIAGRAM
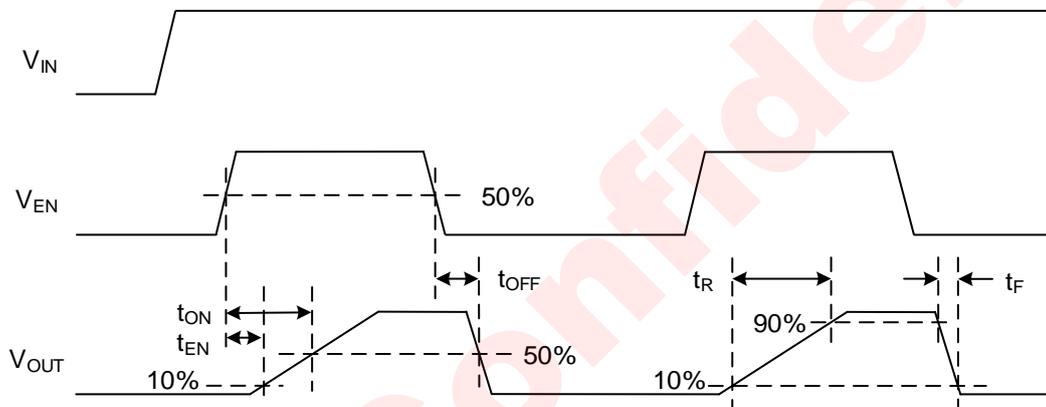
Figure 5   AW3512/AW35122 Timing Diagram

TYPICAL CHARACTERISTICS

Ambient temperature is 25°C, C_{IN} = C_{OUT}=1µF, unless otherwise noted.
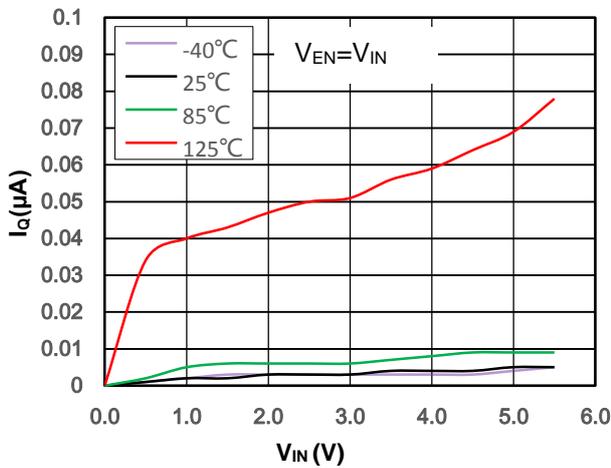
Figure 6   Quiescent Current vs. V_{IN}, No load
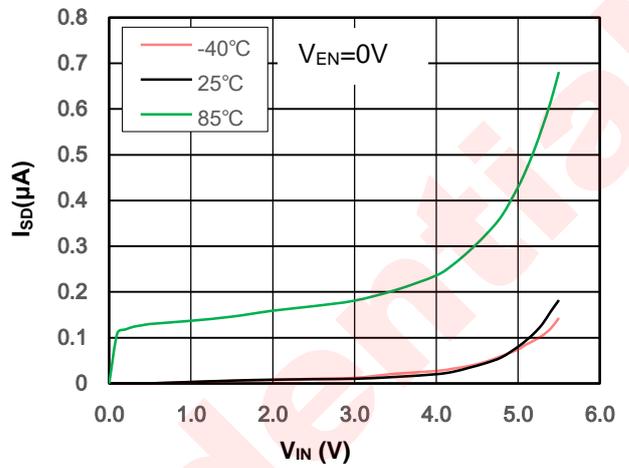
Figure 7   IN Shutdown Current vs. V_{IN}
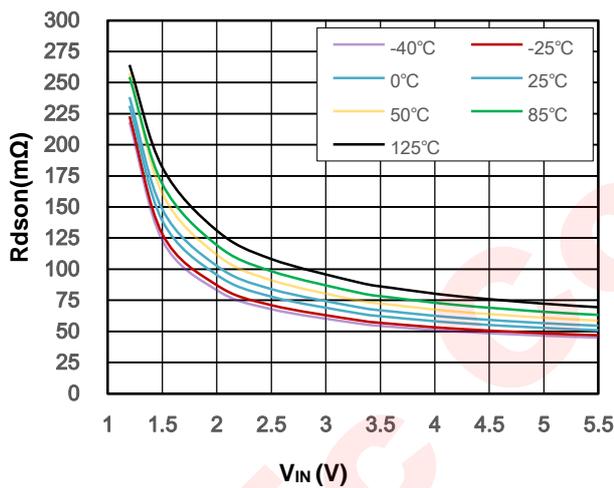
Figure 8   Rdson vs. V_{IN}(I_{OUT}=200mA)
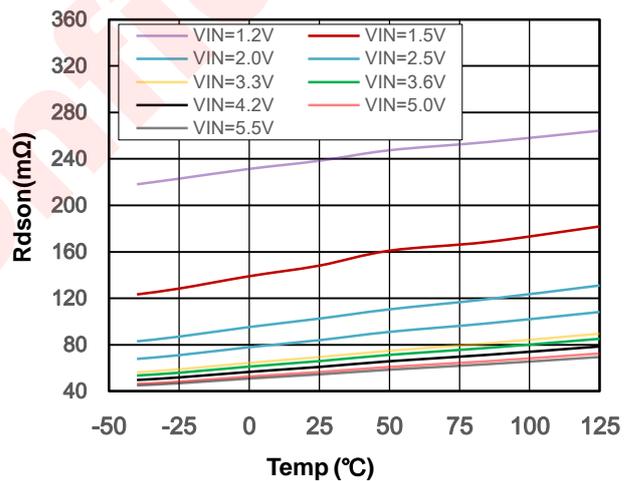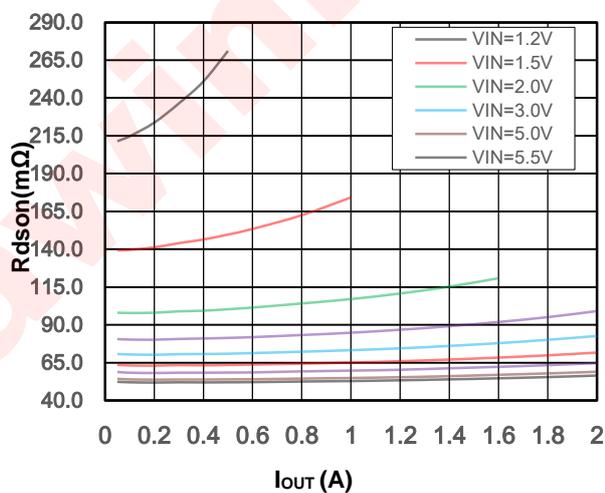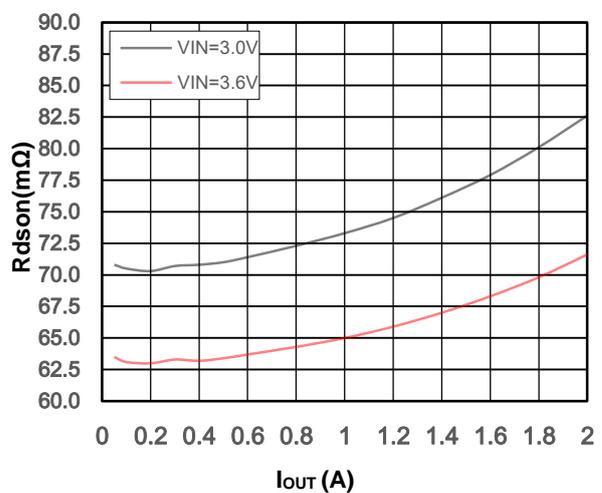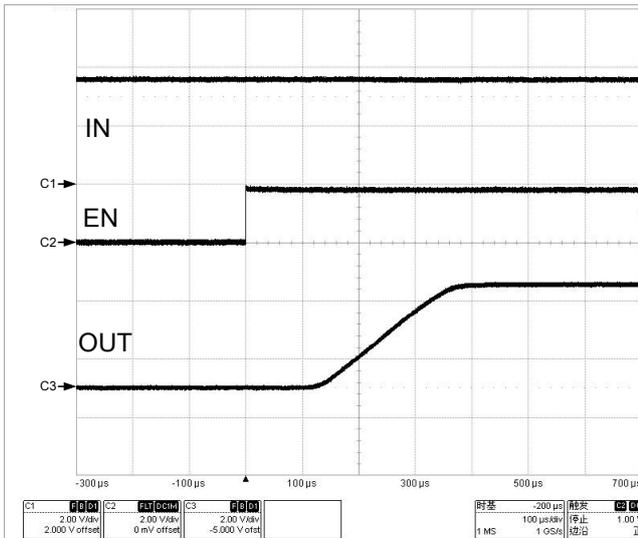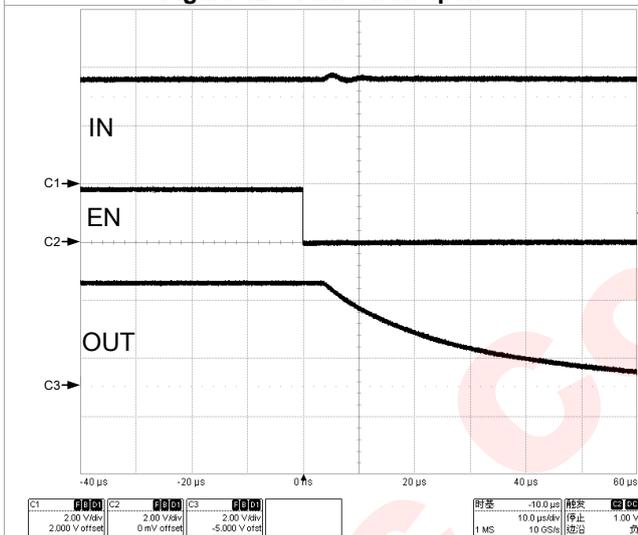

Figure 9   Rdson vs. Temperature(I_{OUT}=200mA)

Figure 10   Rdson vs. I_{OUT}

Figure 11   Rdson vs. I_{OUT}

V_{IN}=3.6V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 12   Turn On Response
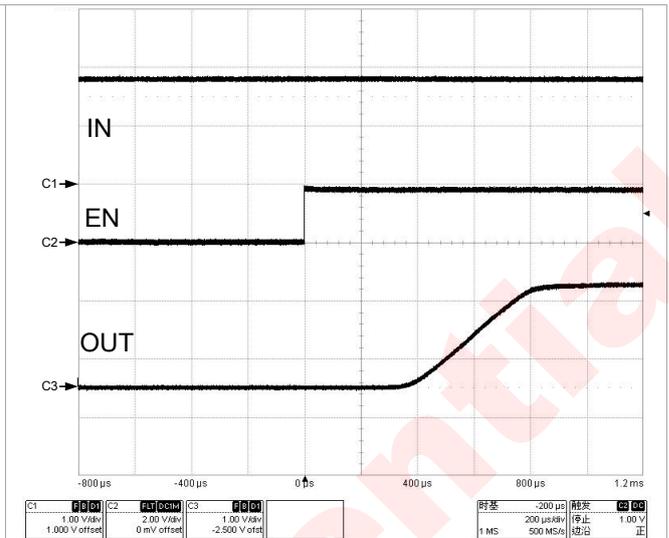
V_{IN}=1.8V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 13   Turn On Response

V_{IN}=3.6V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 14   Turn Off Response(AW3512)
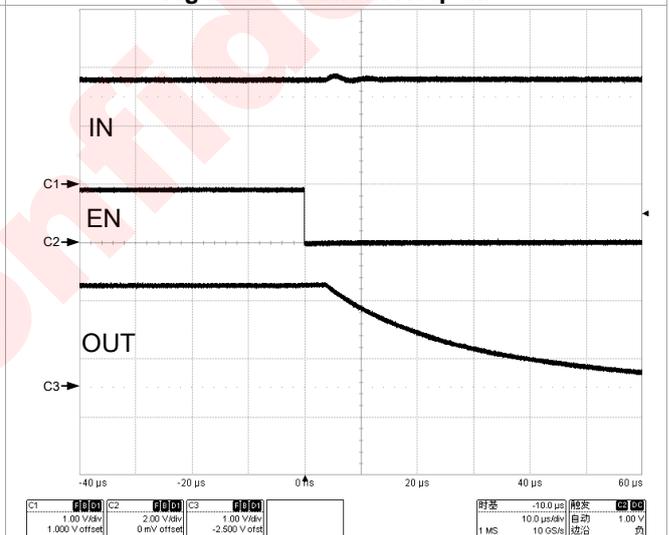
V_{IN}=1.8V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 15   Turn Off Response(AW3512)

V_{IN}=3.6V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 16   Turn Off Response(AW35122)

V_{IN}=1.8V，C_{IN}=1µF，C_{OUT}=1µF，R_{load}=30Ω
Figure 17   Turn Off Response(AW35122)
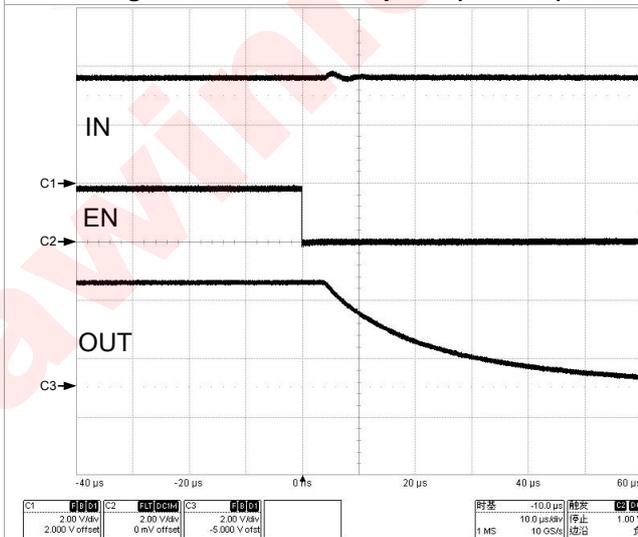
$V_{IN}=3.6V$，$C_{IN}=1\mu F$，$C_{OUT}=1\mu F$，no R_{load}
Figure 18   Inrush Current with $C_{OUT}=1\mu F$
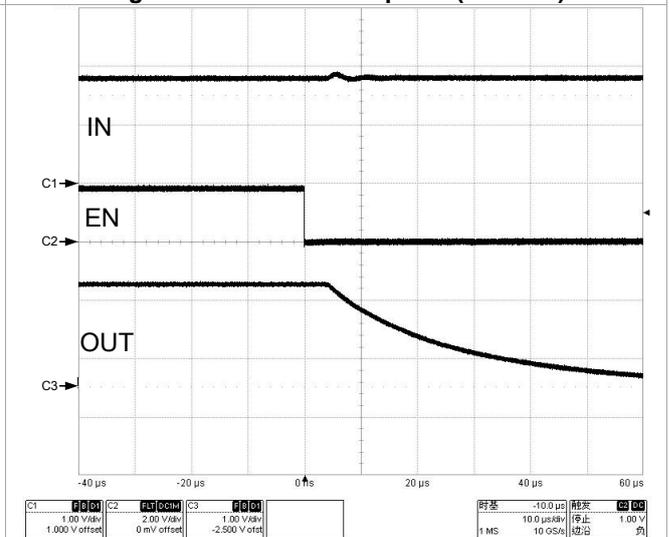
$V_{IN}=1.8V$，$C_{IN}=1\mu F$，$C_{OUT}=1\mu F$，no R_{load}
Figure 19   Inrush Current with $C_{OUT}=1\mu F$
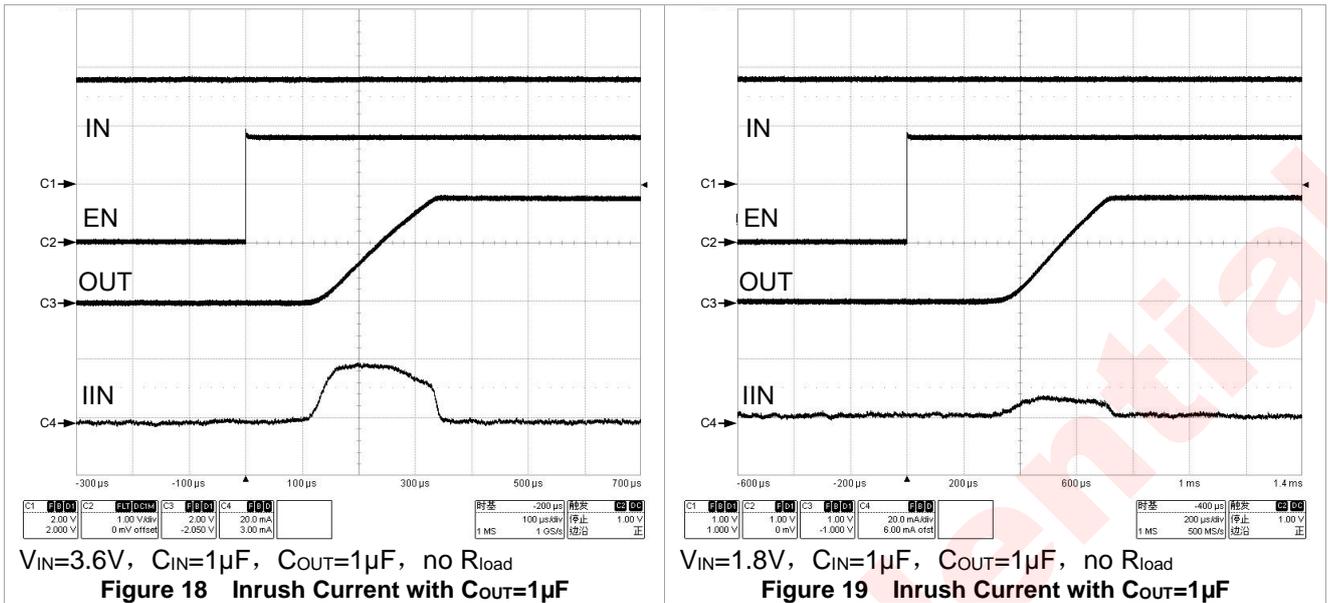
DETAILED FUNCTIONAL DESCRIPTION

The AW3512/AW35122 integrates a high side P channel MOSFET load switch, and provides a low on-resistance for a low voltage drop across the device. A controlled slew rate is used in applications to limit the inrush current. The part can be turned on, with a supply voltage from 1.2V to 5.5V.

TURN ON/OFF CONTROL

Enable pin is an active high. The device is opened when EN pin is tied low (disable) or pulled down by internal 7.1MΩ resistor(AW35122), forcing PMOS switch off. The IN/OUT path is activated with a minimum of Vin of 1.2V and EN forced to high level.

Table 1. Functional Table

EN	IN to OUT	OUT to GND
Low	OFF	ON
High	ON	OFF

SLEW RATE CONTROL

When the switch is enabled, the device regulates the gate voltage of MOSFET, and controls the V_{OUT} slew rate during t_R to avoid a large input inrush current. The feature reduces the interference to the power supply.

QUICK OUTPUT DISCHARGE

The AW3512/AW35122 includes the Quick Output Discharge (QOD) feature, in order to discharge the application capacitor connected on OUT pin. When EN pin is set to low level (disable state), a discharge resistance with a typical value of 276Ω(AW35122: 75Ω) is connected between the output and ground, pull down the output and prevent it from floating when the device is disabled.

APPLICATION INFORMATION

POWER SUPPLY RECOMMENDATIONS

The device is designed to operate with a V_{IN} range of 1.2V to 5.5V. This supply must be well regulated and placed as close to the device terminals as possible. It must also be able to withstand all transient and load currents, using a recommended input capacitance of 1μF if necessary. If the supply is located more than a few inches from the device terminals, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. If additional bulk capacitance is required, an electrolytic, tantalum, or ceramic capacitor of 10μF may be sufficient.

MANAGING INRUSH CURRENT

When the switch is enabled, the output capacitors must be charged up from 0V to V_{IN}. A input inrush current will appear. The Inrush current can be calculated using Equation 1:

$$\text{Iinrush} = \text{C}_{\text{OUT}}\frac{\text{dV}_{\text{OUT}}}{\text{dt}} \tag{1}$$

where:

- C_{OUT} = Output capacitance

- Dv_{OUT} = Output voltage, equals to V_{IN}

- dt = Rise time t_R.

The AW3512/AW35122 offers a controlled slew rate for minimizing inrush current.

POWER DISSIPATION

The power dissipation produced by the power MOSFET Rdson in ON-state can be calculated with the following equation:

$$\text{P}_{\text{D}} = \text{Rdson}\times\left(\text{I}_{\text{OUT}}\right)^2 \tag{2}$$

Where:

- P_D = Power dissipation (W)

- R_{dson} = Power MOSFET on resistance (Ω)

- I_{OUT} = Output current (A)

THERMAL CONSIDERATIONS

Main contributor in term of junction temperature $T_J(max)$ is the power dissipation, and $T_J(max)$ should be restricted to 125˚C under ON-state. Junction temperature is directly proportional to power dissipation in the device, it can be calculated by the following equation:

$$\text{T}_{\text{J}} = \text{T}_{\text{A}} + \text{R}_{\theta\text{JA}}\times\text{P}_{\text{D}} \tag{3}$$

where:

- T_J = Junction temperature of the device

- T_A = Ambient temperature

- P_D = Power dissipation of the device

- $R_{\theta JA}$ = Junction to ambient thermal resistance. This parameter is highly dependent on board layout.

PCB LAYOUT CONSIDERATION

AW3512/AW35122 is a low ON-Resistance load switch, to obtain the optimal performance, PCB layout should be considered carefully. Here are some guidelines:

1. All the peripherals should be placed as close to the device as possible. Place the input capacitor C_{IN} on the top layer (same layer as the AW3512/AW35122) and close to IN pin, and place the output capacitor C_{OUT} on the top layer (same layer as the AW3512/AW35122) and close to OUT pin.

2. The AW3512/AW35122 integrate an up to 1.5A rated PMOS FET, and the PCB design rules must be respected to properly evacuate the heat out of the silicon. By increasing PCB area, especially around IN and OUT pins, the $R\theta_{JA}$ of the package can be decreased, allowing higher power dissipation. Red bold paths on Figure 18 are power lines that will flow large current, please route them on PCB as straight, wide and short as possible.

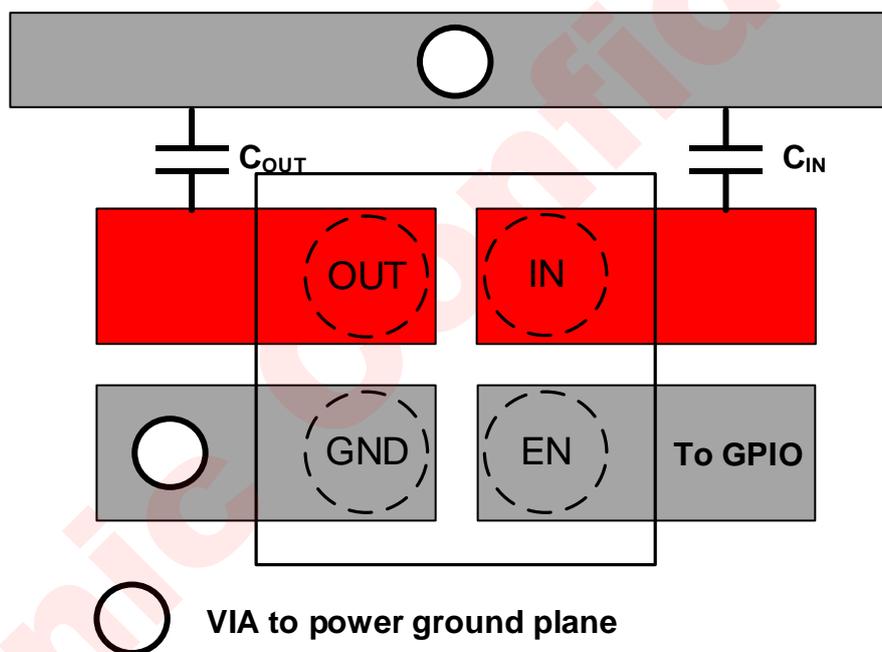3. Use rounded corners on the power trace from the power supply connector to AW3512/AW35122 to decrease EMI coupling.
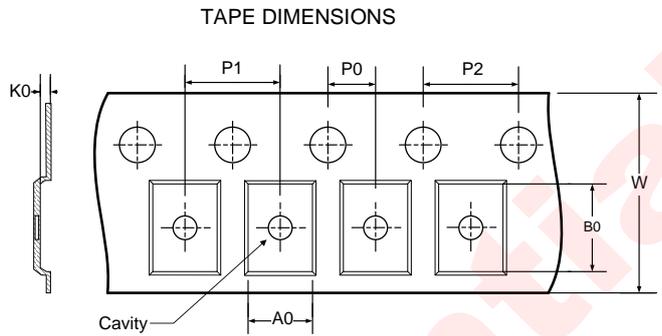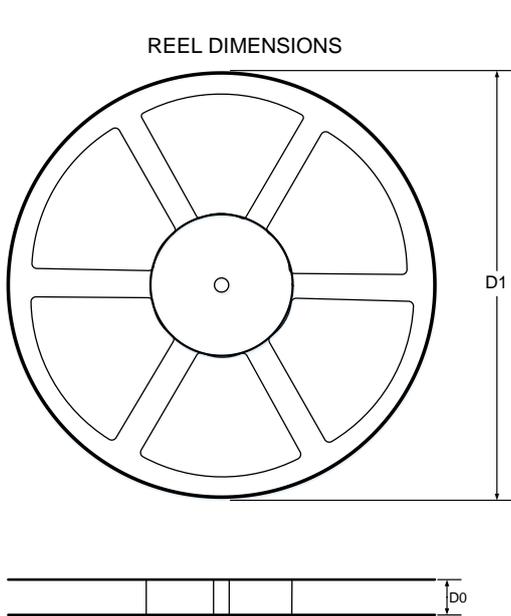

Figure 20　PCB layout example

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TAPE DIMENSIONS

A0：Dimension designed to accommodate the component width
B0：Dimension designed to accommodate the component length
K0：Dimension designed to accommodate the component thickness
W：Overall width of the carrier tape
P0：Pitch between successive cavity centers and sprocket hole
P1：Pitch between successive cavity centers
P2：Pitch between sprocket hole
D1：Reel Diameter
D0：Reel Width

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

Pin 1

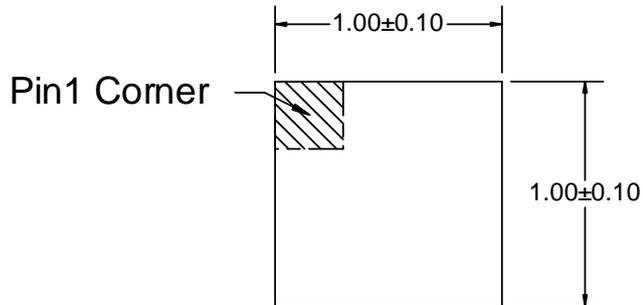Sprocket Holes

User Direction of Feed
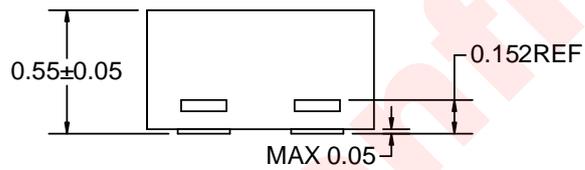
Pocket Quadrants
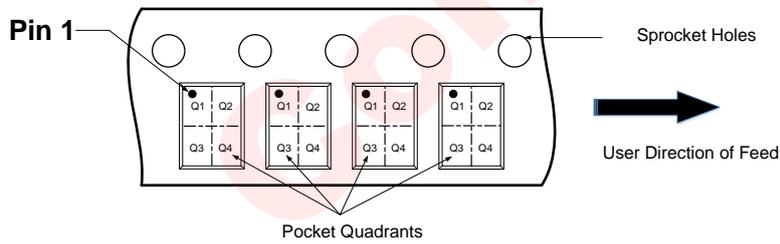
DIMENSIONS AND PIN1 ORIENTATION

D1 (mm)	D0 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
178	8.4	1.16	1.16	0.74	2	2	4	8	Q1

All dimensions are nominal

PACKAGE DESCRIPTION

Pin1 Corner

1.00±0.10

1.00±0.10

TOP VIEW

0.55±0.05

0.152REF

MAX 0.05

SIDE VIEW

0.50BSC

1   2

B

0.50BSC

SYMM
℄

A

0.23±0.05

3X(Φ 0.23±0.05)

0.23±0.05

SYMM
℄
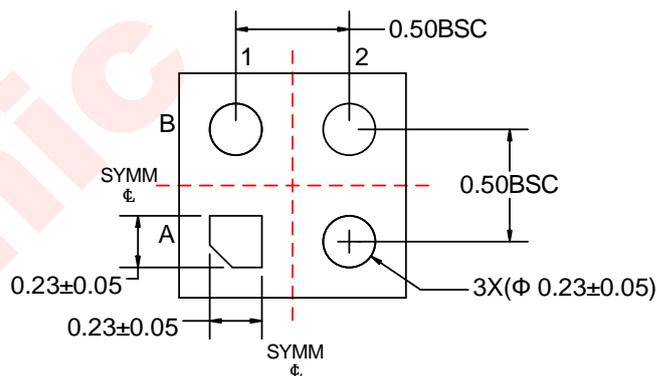
BOTTOM VIEW

Unit: mm

AW3512FDR PACKAGE DESCRIPTION

1.00±0.10

Pin1 Corner

1.00±0.10

TOP VIEW

0.55±0.05

0.152REF

MAX 0.05

SIDE VIEW

0.50 TYP

B

0.50 TYP

SYMM ₵

A

4X(Φ 0.23±0.05)

1   2

SYMM ₵
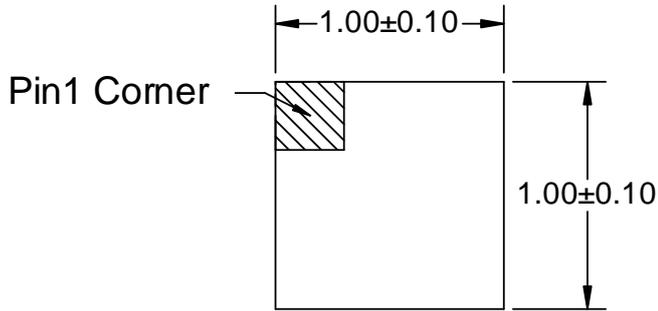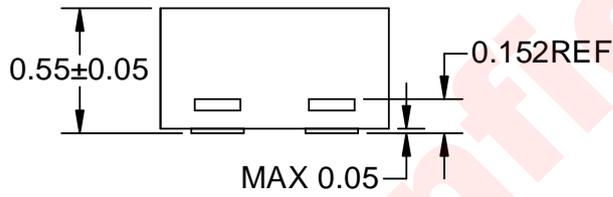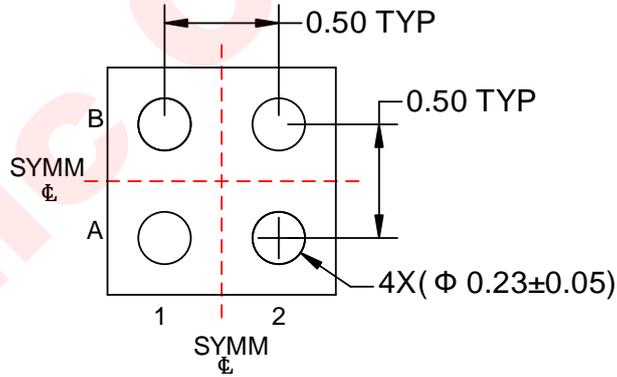
BOTTOM VIEW

Unit: mm

AW35122FDR PACKAGE DESCRIPTION

LAND PATTERN DATA

4X(Φ 0.23)

0.50 TYP

1   2

A

SYMM
℄

0.50 TYP

B

SYMM
℄

0.05 MAX
All AROUND

SOLDER MASK
OPENING

METAL

NON SOLDER MASK DEFINED

0.05 MIN
All AROUND

SOLDER MASK
OPENING

METAL UNDER
SOLDER MASK

SOLDER MASK DEFINED
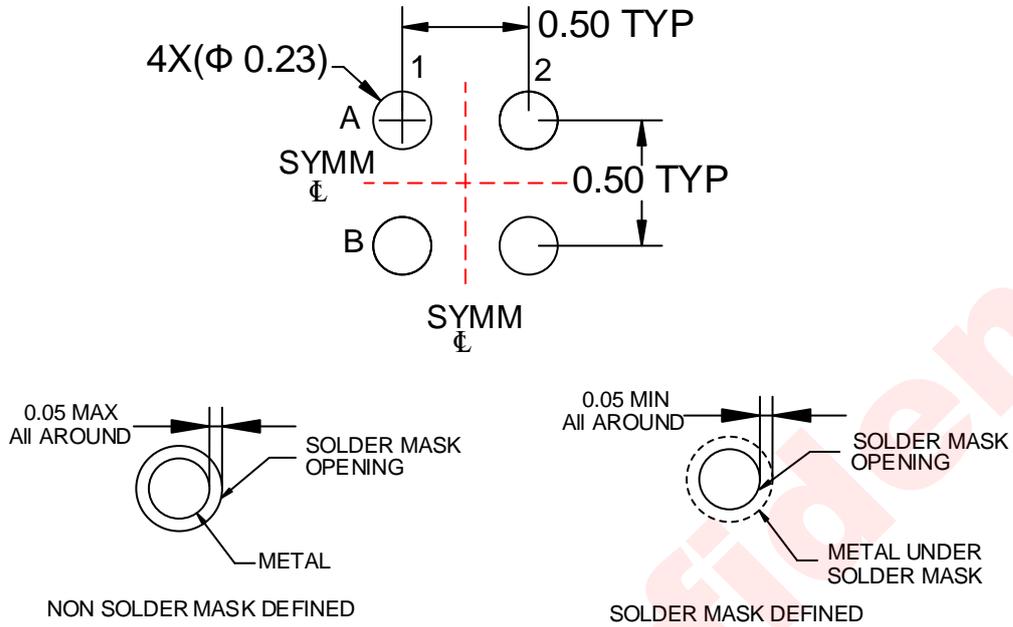
Unit: mm

REVISION HISTORY

Version	Date	Change Record
V1.0	July 2019	Datasheet V1.0 Released

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